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# Understanding the role of 5d electrons in ferromagnetism and spin-based transport properties of $K_2W(Cl/Br)_6$ for spintronics and thermoelectric applications

 Mukaddar Sk \* and Saurabh Ghosh\*

In this article, we have systematically investigated the structural, electronic, magnetic, and spin-based thermoelectric properties of  $K_2W(Cl/Br)_6$  by first-principles calculation. The obtained negative formation energy confirmed the thermodynamic stability of  $K_2W(Cl/Br)_6$ , while the tolerance factor calculation showed their cubic phase stability. In addition, we have estimated the elastic constants which confirmed the mechanical stability of  $K_2W(Cl/Br)_6$ . Further, the spin-polarized band structure and density of states calculations revealed the half-metallic nature with high Curie temperature ( $T_c$ ) values of 613 K and 597 K for  $K_2WCl_6$  and  $K_2WBr_6$ , respectively. Moreover, we have studied the temperature variation of thermoelectric properties such as  $k_{\parallel}$ ,  $\sigma$ ,  $k_e$ ,  $S$ ,  $PF$ , and  $ZT$ . Such results showed that higher  $ZT$  values for spin-down channels are obtained from ultra-low  $k_e$  and high  $PF$ . Therefore,  $K_2W(Cl/Br)_6$  are viable thermoelectric and spintronic materials.

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## 1. Introduction

The advancement of spintronics and quantum computing technology has boosted the memory storage speed with multi-functional characteristics. This is a developing field which reduces magnetic chip size and enhances the memory speed by utilizing the electron spin and its charge.<sup>1,2</sup> The advanced spintronic technology also has novel achievements in non-volatile magnetic random-access memory.<sup>3,4</sup> These advancements can also be applied in electronic devices due to their low cost, faster data speed, and less power consumption.<sup>5-7</sup> In addition, the recent quantum technology takes advantage of electronic spin states in the digital display rather than the charge states of a typical electronic operation. The development of giant magnetic resistance (GMR) in 1998 boosted this technology,<sup>8</sup> where the electron spin can create an enormous difference in the resistance of alternative magnetic layers in the presence of external applied magnetic fields. Thus, the magnetic response of electronic charge and spin facilitate the low-powered, high-speed, non-volatile, and nano-size memory.<sup>9,10</sup>

The present scientific achievements of spintronics technology gave rise to the improvement of magneto-resistive random-access memory (MRAM), magnetic sensors, magnetic valves, read heads of magnetic hard drives, and giant magneto-

resistive effect (GMR). Materials exhibiting the high spin polarization (SP) are suitable candidates for spintronics technology. Rather, for the half-metallic ferromagnetism (HMF) materials, one channel is metallic and the other one is insulating, which produces 100% SP, demonstrating that they are spintronics materials.<sup>11,12</sup> The first HMF was observed by de Groot *et al.* in Heusler alloy PtMnSb and NiMnSb in 1983.<sup>13</sup> After this, HMF was observed in many types of materials such as diluted magnetic semiconductors, perovskites, spinel chalcogenides, and double perovskites.<sup>14,15</sup> But, the major confront of spintronic materials are their phase instability at elevated temperature and clustering of magnetic ions greatly influences the functionality of spin. In later research, the phase instability issue was resolved at higher temperature, but the problem of clustering remains to be addressed. Nonetheless, a lot of transition-metal doped alloys were formed at room temperature, still the issue of clustering limits their applications.<sup>16</sup> To solve the problem of spin segregation, numerous procedures were adopted, where the doping of nonmagnetic elements into alloys is prominent. The FM behaviour has been reported in  $Be_{1-x}C_xS$ ,<sup>17</sup>  $Sn_{1-x}Mg_xO_2$ ,<sup>18</sup> *etc.* But these materials are expensive and have complicated production procurements.

Recently, Halide based double perovskites with chemical formula  $X_2YZ_6$  ( $X = Cs, Rb, K$ ;  $Y = Os, Nb, Ta, W$ ;  $Z = Cl, Br, I$ ) have attracted considerable attention for spintronics applications due to their low cost, high Curie temperature ( $T_c$ ), and good stability.<sup>19-23</sup> In  $X_2YZ_6$ , the d-orbital electrons of Y atom contributes significantly to the magnetic moment. Furthermore, it has been noted that the halide based double

Department of Physics and Nanotechnology, SRM Institute of Science and Technology, Kattankulathur, 603 203, Tamil Nadu, India. E-mail: mukaddarsk05@gmail.com; saurabhghosh2802@gmail.com



perovskites have ferromagnetism at high Curie temperature. However, there is a lack of detailed description on the physical properties of  $X_2YZ_6$ . In this article, we have taken  $K_2W(Cl/Br)_6$  compounds to investigate their magnetic and spin-based transport properties by first-principles calculation. These  $K_2W(Cl/Br)_6$  compounds have been prepared by Xu *et al.* and Epperson *et al.* from a stoichiometric mixture of  $K(Cl/Br)$  and  $W(Cl/Br)_4$  and they have observed the cubic phase stability from the X-ray diffraction patterns.<sup>24,25</sup> However, existing literatures about these compounds are only limited to their structural studies. To the best of our knowledge, there is no detailed report available on magnetic and spin-based transport properties of  $K_2W(Cl/Br)_6$ . Our spin-polarized band structure and density of states calculations revealed the presence of half-metallic character in these materials with high Curie temperature. Thus,  $K_2W(Cl/Br)_6$  compounds are emerging spintronics materials.

Besides spintronics applications, the lead-free halide based double perovskites have attracted considerable attention for photovoltaic and thermoelectric technology. A good photovoltaic material should have high optical absorption coefficient and conductivity, with low reflectivity. On the other hand, a material is efficient for thermoelectric technology, if it has high Seebeck coefficient ( $S$ ), good electrical conductivity ( $\sigma$ ), and low thermal conductivity ( $k$ ).<sup>26</sup> Many lead-free halide based double perovskites are reported to have suitable photovoltaic and thermoelectric properties. For instance, Haq *et al.* predicted that  $Rb_2XGaBr_6$  ( $X = Na, K$ ) are promising photovoltaic and thermoelectric materials due to their optimum optical absorption coefficient and large  $ZT$  values, respectively.<sup>52</sup> Later, Iqbal *et al.* have shown the emerging photovoltaic and thermoelectric properties of  $Rb_2AlInX_6$  ( $X = Cl, Br, I$ ) due to their narrow band gap.<sup>53</sup> Also, Nawaz *et al.* reported that  $Rb_2YInX_6$  ( $X = Cl, Br, I$ ) are thermodynamically stable and they are suitable for photovoltaic and thermoelectric technology.<sup>54</sup> Instead of low thermal conductivity arising from the occupation of cations in the octahedral structure, it is very surprising that these halide based double perovskites are mainly studied for photovoltaic purposes. Only very few experimental studies were performed to investigate their thermoelectric properties and interestingly the research in the thermoelectric response is now growing.<sup>27</sup> In this article, we have carried out the spin-based thermoelectric properties of  $K_2W(Cl/Br)_6$ . We have computed the temperature variation of  $k_f$ ,  $\sigma$ ,  $k_e$ ,  $S$ , PF, and  $ZT$ . The higher  $ZT$  values for spin-down channels have resulted from ultra-low  $k_e$ , and high PF. Thus,  $K_2W(Cl/Br)_6$  are potential thermoelectric and spintronic materials.

## 2. Computational details

The electronic structure, magnetic properties and transport properties of  $K_2W(Cl/Br)_6$  were investigated by using Wien2k<sup>28</sup> and BoltzTraP code.<sup>29</sup> We have employed PBEsol approximation to optimize the crystal structure in FM and AFM states.<sup>30</sup> However, PBEsol approximation underestimates the electronic bandgap on which magnetic and transport properties are dependent. Therefore, we have employed TB-mBJ formalism,<sup>31</sup> which can accurately predict the bandgap. In addition, due to

the presence of heavy elements, SOC coupling is significant, that was added with TB-mBJ. The energy cut-off for geometry optimization was selected to be 520 eV. On the other hand, the average forces per ions were optimized to 0.002 eV  $\text{\AA}^{-1}$ . Furthermore, we have considered a  $k$  mesh of  $12 \times 12 \times 12$  for electronic calculation. The product of maximum wave vector and muffin tin radii is kept as  $R_{MT} \times K_{max} = 8$ , along with angular momentum vector  $l = 10$  and Gaussian factor = 10. The level convergence is achieved to be  $10^{-5}$  Ry self consistently by using the above-mentioned inputs. For transport properties calculation, we have considered a dense  $k$ -points of 150 000.

## 3. Results and discussion

### 3.1 Structural and mechanical stabilities

The halide based double perovskites  $K_2W(Cl/Br)_6$  have a cubic phase with space group  $Fm\bar{3}m$  (225).<sup>32</sup> The perspective view of  $K_2W(Cl/Br)_6$  is shown in Fig. 1. The vacancies between the octahedra  $W(Cl/Br)_6$  are occupied by K atoms whereas each octahedron is separated by the other octahedra through the 12-fold coordination system of (Cl/Br). In this structure, each K atom is surrounded by 12 (Cl/Br) atoms, whereas every W atom is coordinated with 6 (Cl/Br) atoms. Moreover, each  $W(Cl/Br)_6$  is located at the corner and face center of the cubic system. The K, W, and (Cl/Br) atoms in the unit cells of both systems are positioned at (0.25, 0.25, 0.25) (0, 0, 0) and (x, 0, 0), respectively. The atomic positions in the structure are corrected by minimizing strain throughout the optimization process.

The optimized energy *versus* volume plot is shown in Fig. 2(a and b). It is noticeable from Fig. 2(a and b), that  $K_2W(Cl/Br)_6$  compounds have positive energy difference between FM and AFM states indicates that the FM is more preferable because of more energy release in this process.

Curie temperature ( $T_c$ ) of  $K_2W(Cl/Br)_6$  are predicted through the Heisenberg classical model. *e.*,  $T_c = 2\Delta E/3xK_B$ , where  $x$  is the contribution of W atom and  $\Delta E$  is the energy difference between ferromagnetic and antiferromagnetic ground states, *i.e.*  $\Delta E = E_{AFM} - E_{FM}$ .<sup>33,34</sup> The computed  $T_c$  values are 613 K and 597 K for  $K_2WCl_6$  and  $K_2WBr_6$ , respectively. The high  $T_c$  values make these compounds suitable for spintronic applications.

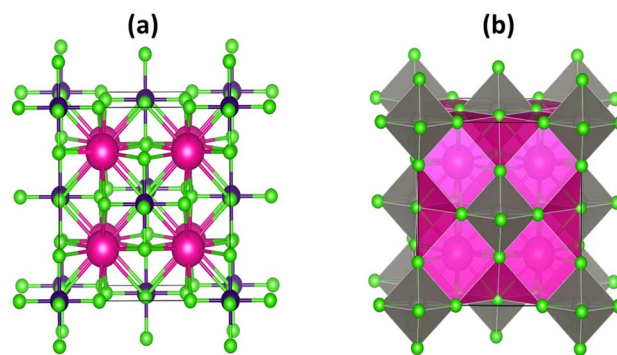


Fig. 1 The crystal structure (a) atomic and (b) polyhedral forms of  $K_2W(Cl/Br)_6$  with magenta, blue and green colors represent the K, W, and (Cl/Br) atoms respectively.

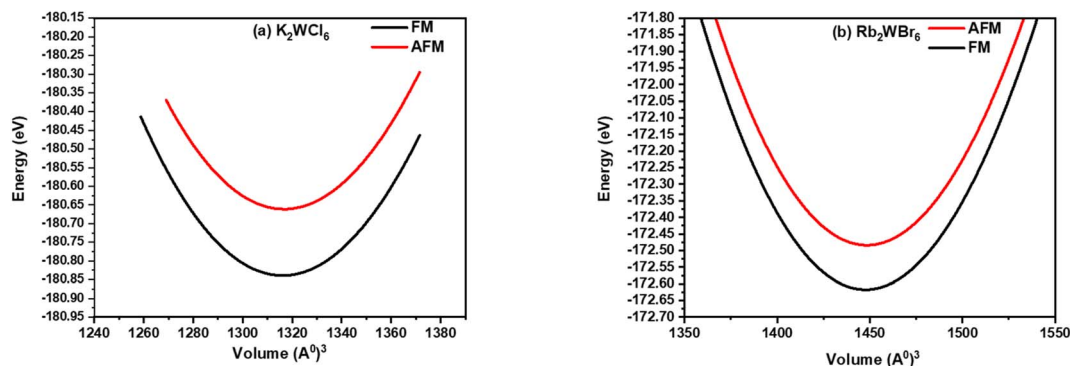


Fig. 2 Volume optimization plot of (a)  $K_2WCl_6$  and (b)  $K_2WBr_6$  in FM (black line) and AFM (red line) calculated through PBEsol approximation.

The cubic phase stability of  $K_2W(Cl/Br)_6$  are investigated from Goldsmith tolerance factor or calculation as follows.

$$\tau = 0.707 \frac{(R_A + R_X)}{(R_B + R_X)} \quad (1)$$

It is worthy to mention here that, the stable cubic phase should have  $\tau$  value in the range of 0.9–1.02.<sup>35</sup> Table 1 clearly shows that  $\tau$  values of  $K_2W(Cl/Br)_6$  are in this range demonstrating their cubic phase stability.

To investigate the synthetic possibility of  $K_2W(Cl/Br)_6$ , we have calculated the enthalpy of formation by using the following equation

$$\Delta H_f = E_{\text{total}}\{K_2W(Cl/Br)_6\} - 2E_K^{\text{bulk}} - E_W^{\text{bulk}} - 6E_{(Cl/Br)}^{\text{bulk}} \quad (2)$$

where,  $E_{\text{total}}\{K_2W(Cl/Br)_6\}$ ,  $E_K^{\text{bulk}}$ ,  $E_W^{\text{bulk}}$  and  $E_{(Cl/Br)}^{\text{bulk}}$  represent the ground state energy of  $K_2WX_6$ , K, W, and (Cl/Br) in their bulk form. The predicted values of  $\Delta H_f$  are  $-31.12$  eV and  $-27.12$  eV for  $K_2WCl_6$  and  $K_2WBr_6$ , respectively. This negative  $\Delta H_f$  revealed the thermodynamic stability of  $K_2W(Cl/Br)_6$ .

The mechanical stability was studied from elastic constant values ( $C_{ij}$ ), obtained by using the Cubic Elastic package.<sup>36</sup> It is observed from Table 2 that the values of the various components of  $C_{ij}$  obeyed the Born criteria of mechanical stability, *i.e.*  $C_{11} - C_{12} > 0$ ,  $C_{44} > 0$ ,  $C_{11} + 2C_{12} > 0$ ,  $C_{12} < B < C_{11}$ .<sup>37</sup> Furthermore,

Table 1 The obtained lattice parameter ( $a$ ), tolerance factor ( $\tau$ ), octahedral factor ( $\mu$ ), and formation energy ( $\Delta H_f$ ) of  $K_2W(Cl/Br)_6$

Compound	$a$ (Å)	$\tau$	$\mu$	$\Delta H_f$ (eV)
$K_2WCl_6$	10.71	0.98	0.45	$-31.12$
$K_2WBr_6$	10.75	0.98	0.44	$-27.12$

Table 2 The calculated bulk modulus ( $B$ ), elastic constants ( $C_{ij}$ ), and cauchy pressure (CP) of  $K_2W(Cl/Br)_6$

Compound	$B$ (GPa)	$C_{11}$	$C_{12}$	$C_{44}$	CP
$K_2WCl_6$	41.16	78.19	21.17	18.72	2.45
$K_2WBr_6$	39.33	74.89	20.76	18.41	2.35

we have estimated the Cauchy's pressure ( $CP = C_{12} - C_{44}$ ). The positive value of CP demonstrated the ductile properties of  $K_2W(Cl/Br)_6$ . The overall elastic study confirmed that  $K_2W(Cl/Br)_6$  are mechanically stable.<sup>36</sup>

### 3.2 Magnetic properties

The half-metallic ferromagnetic material having high spin polarization ( $P$ ) is essential for spintronic applications. The spin polarization ( $P$ ) can be obtained as

$$P = \frac{N_{\uparrow}(E_F) - N_{\downarrow}(E_F)}{N_{\uparrow}(E_F) + N_{\downarrow}(E_F)} \times 100 \quad (3)$$

where ( $N_{\uparrow}$ ) and ( $N_{\downarrow}$ ) represent the density of states of up and down the channels at Fermi level ( $E_F$ ). The spin-polarized band structure is shown in Fig. 3. It is noticeable from Fig. 3 that, the quantum state of the spin-up channel overlapped with Fermi level ( $E_F$ ), which demonstrates the metallic nature. However, the spin-down channel shows the insulating nature because of the existence of finite separation between valence band maxima (VBM) and conduction band minima (CBM). Therefore, the combined spin up and spin down showed the half-metallic ferromagnetism nature with 100% spin polarization ( $P = 1$ ). The detailed investigation revealed that the valence band maxima (VBM) and conduction band minima (CBM) of spin-down channels are located at the same  $k$ -point for both compounds, which indicates the direct band gap properties. We have obtained the band gap of 3.01 eV and 2.72 eV for  $K_2WCl_6$  and  $K_2WBr_6$ , respectively in the spin-down channel. Also, the estimated total magnetic moment is calculated to be  $2\mu_B$  for both compounds. The integer value of total magnetic moment implies that  $K_2W(Cl/Br)_6$  are half metallic ferromagnets. Thus,  $K_2W(Cl/Br)_6$  are emerging spintronics materials.

For the detailed investigation of band structure results, we have further calculated the total and partial density of states of  $K_2W(Cl/Br)_6$  as shown in Fig. 4(a–d). It is noticeable from Fig. 4(a and b) that the total DOS in the up spin showed the metallic behavior and the down spin presented the insulating behavior. Therefore,  $K_2W(Cl/Br)_6$  are half-metallic ferromagnetism (HMF) in nature. To investigate the origin of half-metallic ferromagnetism (HMF) in  $K_2W(Cl/Br)_6$ , we have further investigated the partial density of states (PDOS) which is shown in



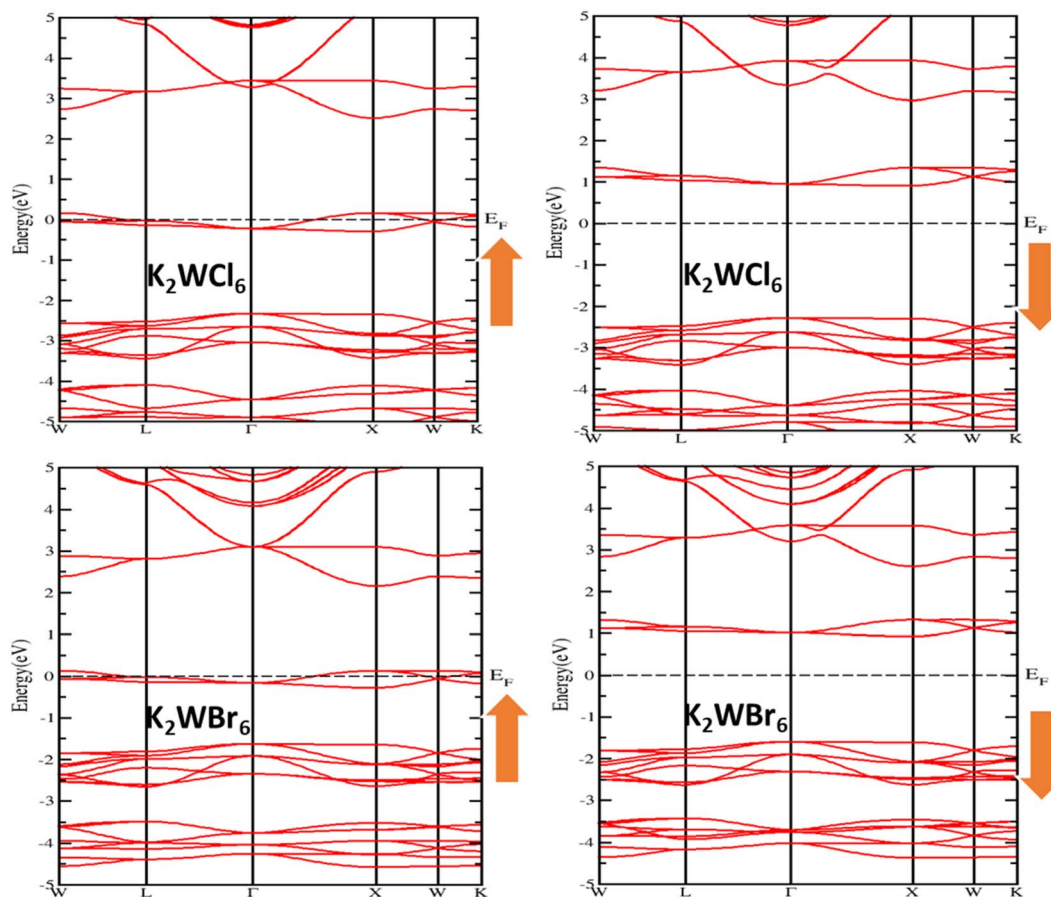


Fig. 3 The spin-polarized band structure of  $K_2W(Cl/Br)_6$  calculated through mBJ + SOC.

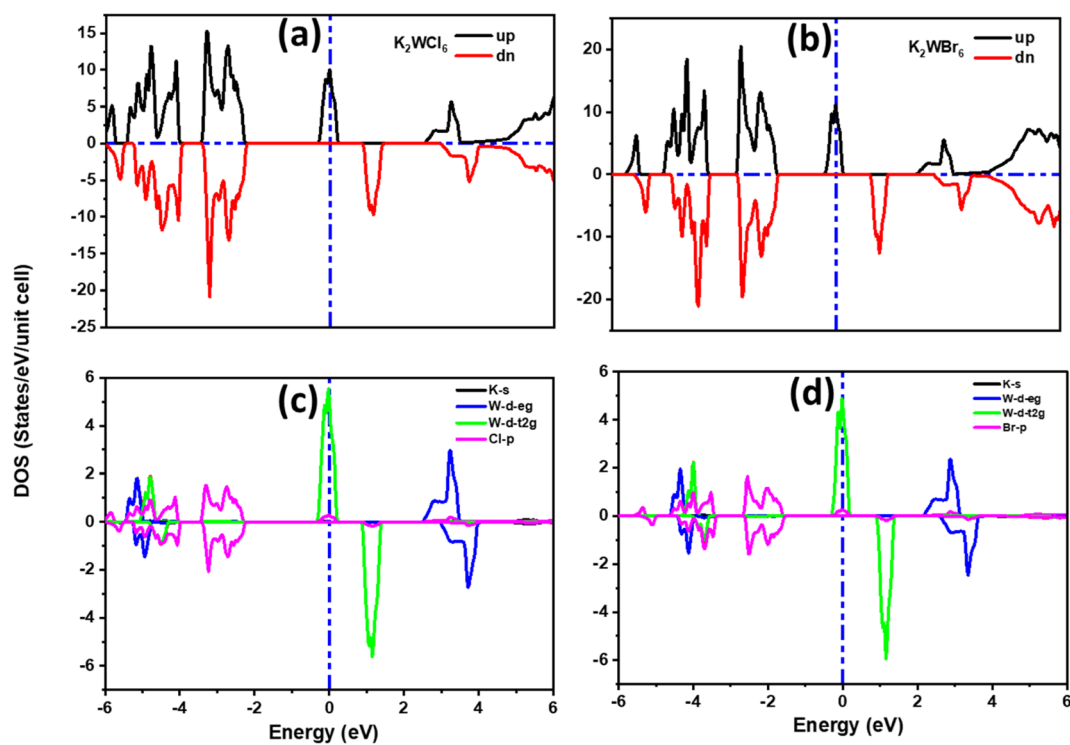


Fig. 4 The spin polarized (a and b) total DOS, (c and d) partial DOS of  $K_2W(Cl/Br)_6$  obtained with mBJ + SOC.



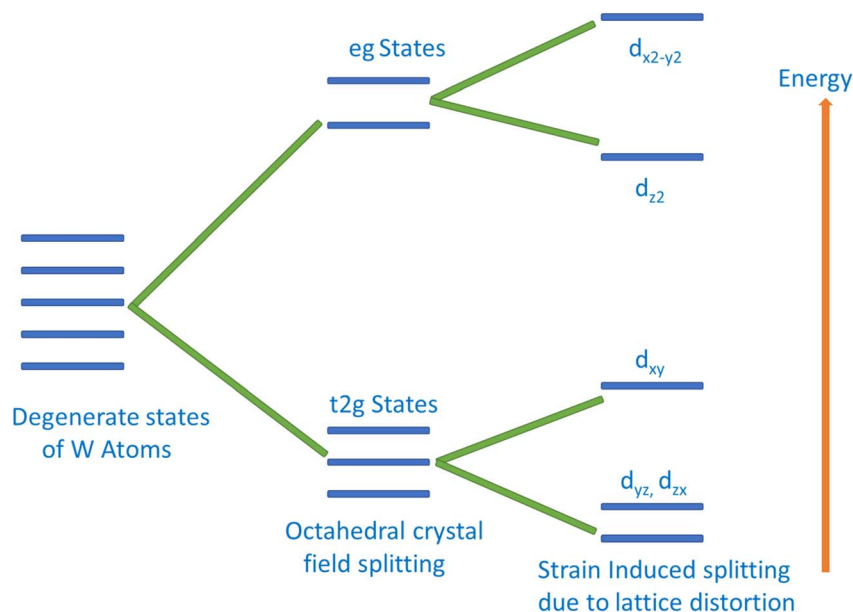


Fig. 5 Schematic representation of crystal-field splitting of W-5d orbital.

Fig. 4(c and d). It is evident from Fig. 4(c and d) that the d- $t_{2g}$  states of W atoms are responsible for introducing HMF in  $K_2W(Cl/Br)_6$ . In the spin-up case, d- $t_{2g}$  states of W atoms overlapped with Fermi level ( $E_F$ ), which produces the metallic nature in  $K_2W(Cl/Br)_6$ . In the spin-down case, d- $t_{2g}$  states move deep into the conduction band and thereby leaving a finite separation between the valence band and conduction band and therefore create insulating nature in  $K_2W(Cl/Br)_6$ .

The magnetic behavior of  $K_2W(Cl/Br)_6$  has also been addressed by an exchange mechanism. The crystal field due to the Coulomb interaction between W and (Cl/Br) atoms split the 5d states of W into  $t_{2g}$  and  $e_g$ . The splitting of W-5d states is schematically shown in Fig. 5. It is clearly noticeable from Fig. 5 that the  $t_{2g}$  is triply degenerate ( $d_{xy}$ ,  $d_{yz}$ ,  $d_{zx}$ ), which has lower energy than the double degenerate  $e_g$  ( $d_{z^2}$ ,  $d_{x^2 - y^2}$ ) states. The splitting of  $e_g$  states results in the upward and downward shifting of  $d_{x^2 - y^2}$  and  $d_{z^2}$ , respectively. At the same time, splitting of  $t_{2g}$  state results in the increase of  $d_{xy}$  state energy and decrease of  $d_{yz}$  and  $d_{zx}$  states energies. The major magnetic response originated from the  $t_{2g}$  state of the W atom. This state is hybridized with the p state of (Cl/Br) *via* double exchange mechanism. Thus, we conclude that the double exchange mechanism between W atoms *via* (Cl/Br) atom is responsible for introducing HMF in  $K_2W(Cl/Br)_6$ .

### 3.3 Thermoelectric properties

Solid-state thermoelectric materials are gaining considerable attraction as novel materials for converting thermal to electrical energy.<sup>38–42</sup> Many mechanical and electronic devices release a huge amount of heat as waste. To take the advantage of wasted heat, efficient thermoelectric materials are needed which can directly convert the wasted heat into electricity. The thermoelectric performance of a material is given by a dimensionless

parameter known as a figure of merit ( $ZT$ ) given by;

$$ZT = \frac{S^2 \sigma T}{(k_e + k_l)}$$

where  $\sigma$ ,  $S$ ,  $T$ ,  $k_e$ , and  $k_l$  represent the electrical conductivity, Seebeck coefficient, temperature, electrical thermal conductivity, and lattice thermal conductivity, respectively. The material with a large  $ZT$  value is considered to be a potential candidate for thermoelectric technology. But, obtaining a large  $ZT$  value is challenging due to the strong correlation of these physical properties. According to a recent report, magnetic interaction is one of the suitable approaches to enhance  $ZT$ .<sup>43–47</sup> The interaction of charge carriers with local magnetic moments, can enhance the carrier effective mass ( $m^*$ ), consequently thermoelectric power ( $S^2 \sigma$ ) and corresponding figure of merit ( $ZT$ ). It is worthy to mention here that such magnetic interaction is present in  $K_2W(Cl/Br)_6$ . Due to the

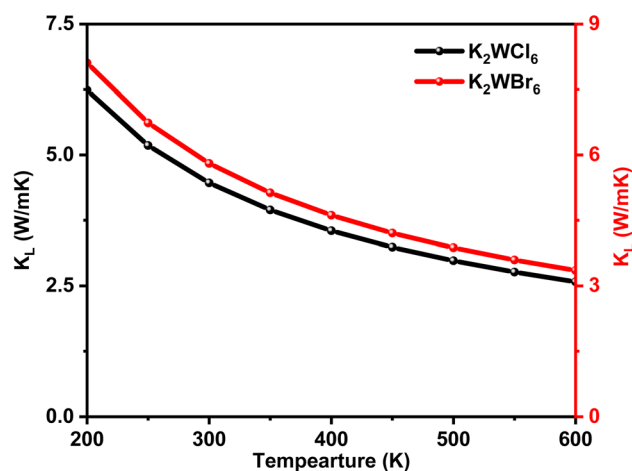


Fig. 6 The temperature-dependent lattice thermal conductivity ( $K_l$ ) of  $K_2W(Cl/Br)_6$  calculated through the Slack equation.



presence of magnetic interaction in  $\text{K}_2\text{W}(\text{Cl}/\text{Br})_6$ , it is expected that these systems will have large  $ZT$  values. However, there are no detailed studies on thermoelectric properties of  $\text{K}_2\text{W}(\text{Cl}/\text{Br})_6$ .

In this article, we have calculated the temperature variation of thermoelectric properties in  $\text{K}_2\text{W}(\text{Cl}/\text{Br})_6$ . For this, we have employed BoltzTrap code.<sup>24</sup> During all calculations, the relaxation time ( $\tau$ ) is fixed by BoltzTraP code as  $\tau = 10^{-14}$  s. We have separately calculated the thermoelectric parameters for spin-up and spindown configurations.

For thermoelectric calculation, the temperature was varied from 200 K to 600 K. The total thermal conductivity ( $k$ ) is the sum of electronic ( $k_e$ ) and lattice ( $k_l$ ) thermal conductivities. A good thermoelectric material should have low  $k$ . The temperature variation of lattice thermal conductivity ( $k_l$ ) was calculated by using the Slack equation.<sup>55</sup> The temperature variation of  $k_l$  is shown in Fig. 6. It can be seen from Fig. 6 that  $k_l$  has an inverse relationship with temperature, which is a typical feature of half-metallic ferromagnetic materials.<sup>48</sup> It is worthy to mention here that  $\text{K}_2\text{W}(\text{Cl}/\text{Br})_6$  compounds have low  $k_l$  values.

The amount of charge flow per unit time inside of a compound can be understood from its electrical conductivity ( $\sigma$ ). The materials are categorized into insulator, semiconductor, and metal-based on their ability of charge flow.<sup>49</sup> A good thermoelectric material should have a large  $\sigma$  value.<sup>50</sup> The temperature variation of  $\sigma$  is calculated for  $\text{K}_2\text{W}(\text{Cl}/\text{Br})_6$  as shown in Fig. (a) and Fig. 8(a), respectively. The detailed analyses revealed that the  $\sigma$  value for spin-up configurations in

$\text{K}_2\text{W}(\text{Cl}/\text{Br})_6$  decreases with temperature until achieving the lowest value of  $1.97 \times 10^5 \Omega^{-1} \text{m}^{-1}$  ( $\text{K}_2\text{WCl}_6$ ) and  $2.25 \times 10^5 \Omega^{-1} \text{m}^{-1}$  ( $\text{K}_2\text{WBr}_6$ ) at 600 K. On the other hand, the values of  $\sigma$  for spin-up states in  $\text{K}_2\text{W}(\text{Cl}/\text{Br})_6$  are almost constant in the entire temperature up to 400 K. However, there was a gradual increase of  $\sigma$  is observed above 400 K. This trend of  $\sigma$  for up and down channels is typical feature in HMF.<sup>51</sup> The detailed investigation reveals that spin-up channel  $\sigma$  is dominant in both cases.

We have also examined the temperature variation of electronic thermal conductivity ( $k_e$ ) as shown in Fig. 7(b) and 8(b) for  $\text{K}_2\text{WCl}_6$  and  $\text{K}_2\text{WBr}_6$ , respectively. It is noticeable that  $k_e$  for spin-up configuration has a direct relation with temperature up to a certain limit where  $k_e$  increases to  $3.41 \text{ W K}^{-1} \text{m}^{-1}$  and  $4.12 \text{ W K}^{-1} \text{m}^{-1}$  respectively for  $\text{K}_2\text{WCl}_6$  and  $\text{K}_2\text{WBr}_6$ , at 400 K. Above this temperature,  $k_e$  decreases gradually for both systems. On the other hand, the values  $k_e$  in spin-down states of  $\text{K}_2\text{W}(\text{Cl}/\text{Br})_6$  are 0.0 in the entire temperature up to 400 K. Above this temperature,  $k_e$  increases abruptly in both cases. It is worthy to mention here that  $k_e$  values for spin-down channels are very less compared to spin-up configuration.

The Seebeck coefficient ( $S$ ) plays an important role to describe the thermoelectric performance. The  $S$  is defined by the ratio of a voltage difference to that of a temperature difference. It can also show the capability of a material to generate the thermo-electromotive force from a given temperature gradient. The  $S$  can be calculated by the following relation

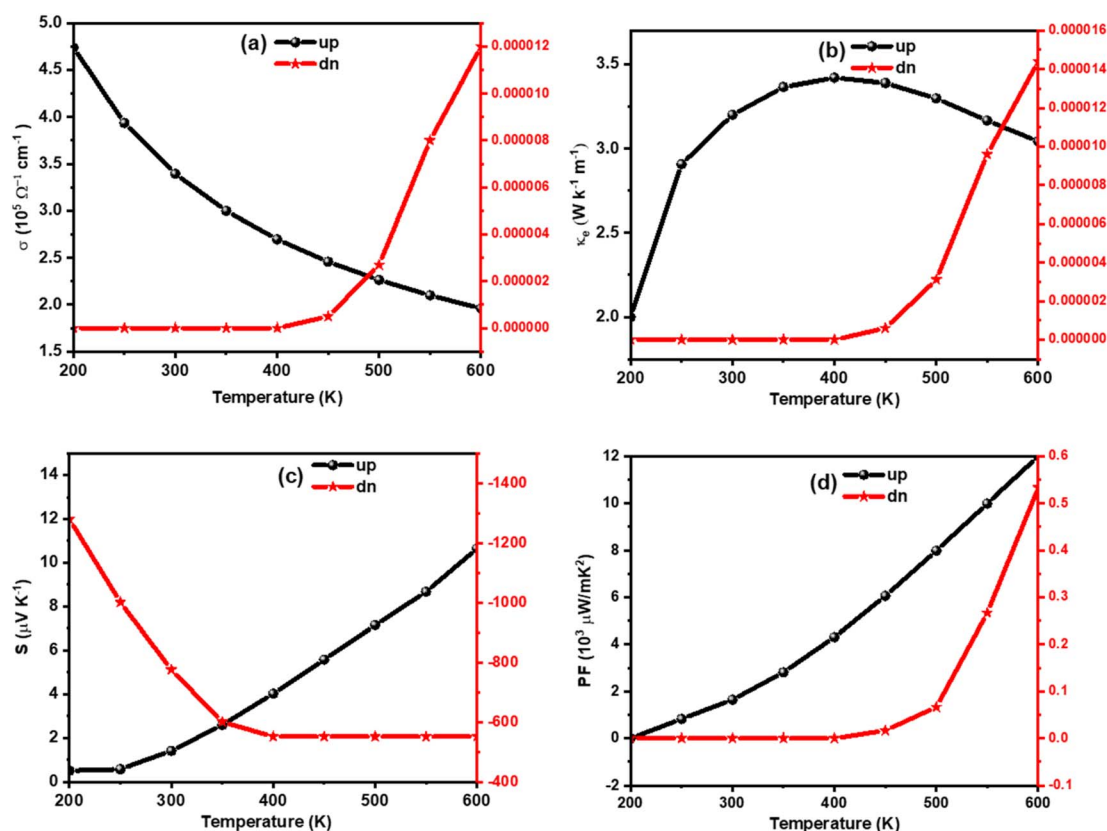


Fig. 7 Calculated (a)  $\sigma$ , (b)  $k$ , (c)  $S$ , and (d) PF of  $\text{K}_2\text{WCl}_6$  as a function of temperature.



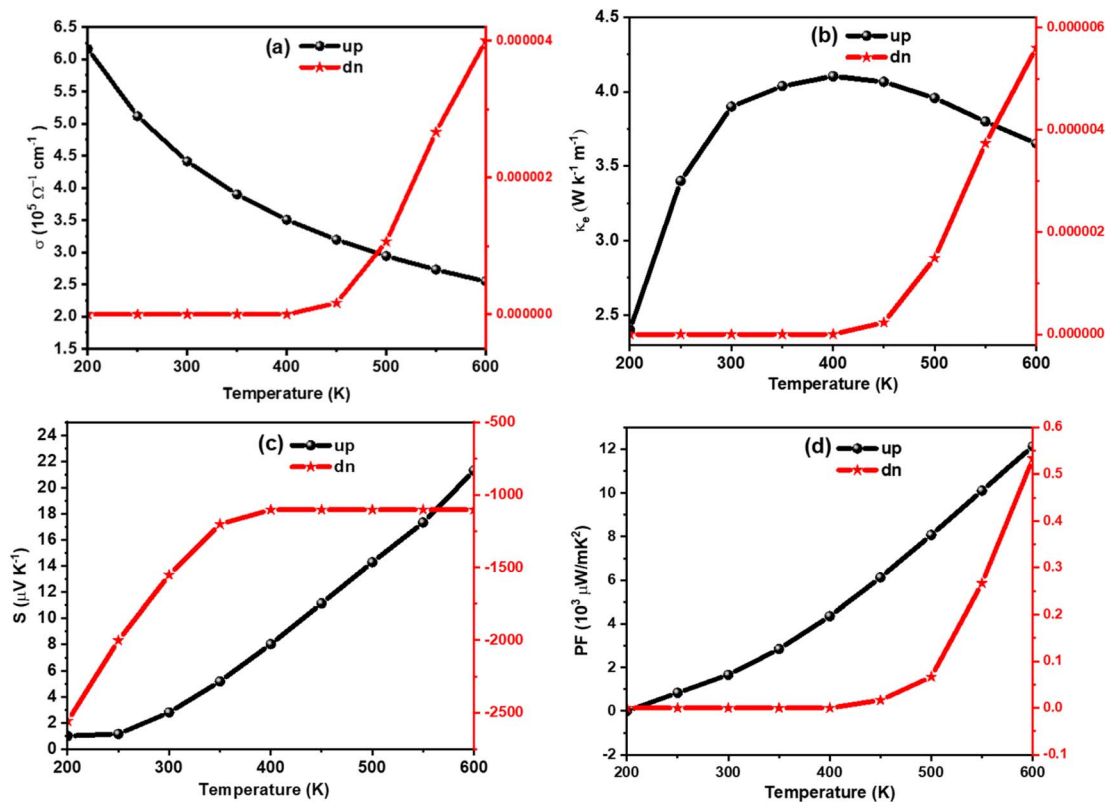


Fig. 8 Calculated (a)  $\sigma$ , (b)  $k$ , (c)  $S$ , and (d) PF of  $K_2WBr_6$  as a function of temperature.

$$S(\uparrow, \downarrow) = \frac{8}{3e^2h} \pi^2 k_B^2 m^*(\uparrow, \downarrow) T \left(\frac{\pi}{3n}\right)^{\frac{2}{3}} \quad (4)$$

where  $h$ ,  $k_B$ ,  $e$ ,  $m^*(\uparrow, \downarrow)$ ,  $T$ , and  $n$  represent the Planck constant, Boltzmann constant, electronic charge, spin-dependent carrier effective mass, absolute temperature, and carrier concentration respectively. A good thermoelectric material should have a large Seebeck coefficient. Fig. 7(c) and 8(c) presented the Seebeck coefficients for both compounds in both spin configurations as a function of temperature. It is noticeable from Fig. 7(c) and Fig. 8(c) that the obtained values of Seebeck coefficients are

positive in the entire temperature range of spin up channels, demonstrating the presence of p-type charge carriers (hole), whereas negative values Seebeck coefficients for a spin up channel suggest the presence n-type charge carriers (electron). The absolute value of  $S$  for spin up configuration in  $K_2WCl_6$  ( $K_2WBr_6$ ) increases from  $0.67 \mu\text{V K}^{-1}$  ( $1.01 \mu\text{V K}^{-1}$ ) at 200 K linearly up to 600 K. This increasing trend in up channel is due to its metallic nature. For metal, there is huge number of free electrons and hence applying a temperature gradient should lead to diffusion of more charge carriers towards cold end. As a result, the potential difference between two ends will increase

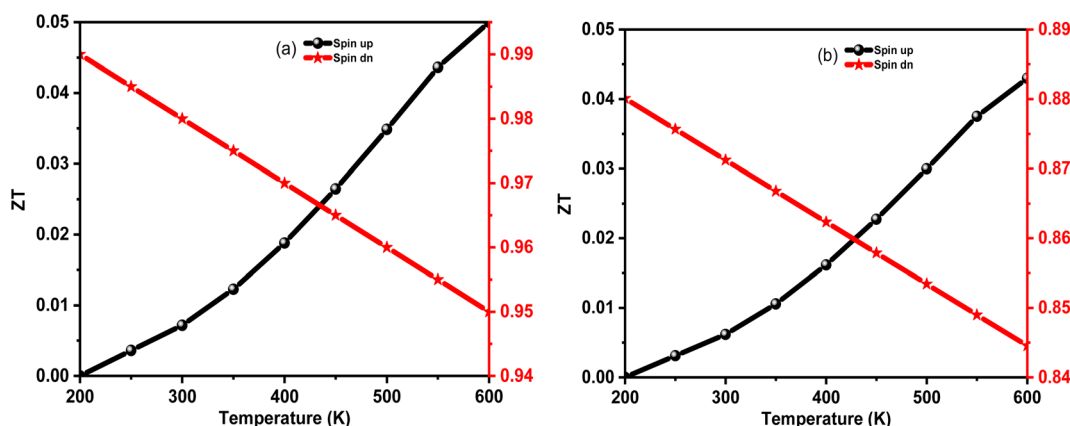


Fig. 9 The calculated ZT value of (a)  $K_2WCl_6$  and (b)  $K_2WBr_6$  as a function of temperature.



and therefore  $S$  will increase. In the spin-down channel, there is an abrupt decrease of  $S$  in  $\text{K}_2\text{WCl}_6$  ( $\text{K}_2\text{WBr}_6$ ) from a very high value of  $1267 \mu\text{V K}^{-1}$  ( $1397 \mu\text{V K}^{-1}$ ) at 200 K beyond this temperature  $S$  decreases gradually. This, decrease trend in spin-down channel can be described from eqn (4). The increasing of temperature can enhance the carrier concentration and thereby decreasing the value of  $S$ . The detailed investigation depicts that spin down channel Seebeck coefficient is dominant in both cases.

In addition, we have calculated the thermoelectric power factor (PF) as shown in Fig. 7(d) and Fig. 8(d). It is noticeable that the PF of spin-up configuration in  $\text{K}_2\text{WCl}_6$  ( $\text{K}_2\text{WBr}_6$ ) increases from  $0.02 \times 10^9 \text{ W mK}^{-1}$  ( $0.01 \times 10^9 \text{ W mK}^{-1}$ ) at 200 K linearly up to 600 K. On the other hand, the PF of spin-down state is found to be  $0.0 \mu\text{W mK}^{-2}$  for both systems in the entire temperature up to 400 K. Beyond this temperature, the PF increases gradually.

Motivated by large  $S$ ,  $\sigma$ , and PF with low  $k_e$ , we have calculated the temperature variation of thermoelectric figure of merit ( $ZT$ ) as Fig. 9(a and b). The detailed analysis revealed that the  $ZT$  for spin upstate in  $\text{K}_2\text{WCl}_6$  ( $\text{K}_2\text{WBr}_6$ ) increases from 0.001 (0.001) at 200 K to 0.05 (0.041) at 600 K. On the other hand,  $ZT$  values of a spin-down channel in  $\text{K}_2\text{WCl}_6$  ( $\text{K}_2\text{WBr}_6$ ) gradually decrease from 0.99 (0.884) at 200 K to 0.95 (0.845) at 600 K. It is noticeable that spin down channel  $ZT$  value is dominant in both cases. The higher  $ZT$  value of the spin-down channel is due to its very low thermal conductivity. Also, the large  $ZT$  values demonstrated that  $\text{K}_2\text{W}(\text{Cl}/\text{Br})_6$  are potential thermoelectric materials.

## 4. Conclusion

To summarize this article, we have systematically investigated the structural, electronic, and thermoelectric properties of  $\text{K}_2\text{W}(\text{Cl}/\text{Br})_6$ . The negative formation energy leads to the thermodynamic stability of  $\text{K}_2\text{W}(\text{Cl}/\text{Br})_6$ . In addition, the spin-polarized band structure and density of states calculations revealed the presence of half-metallic character with higher  $T_c$  values, which are 613 K and 597 K for  $\text{K}_2\text{WCl}_6$  and  $\text{K}_2\text{WBr}_6$ , respectively. Thus,  $\text{K}_2\text{W}(\text{Cl}/\text{Br})_6$  are potential candidates for spintronics application. Furthermore, the origin of half-metallic ferromagnetism is discussed with the double-exchange mechanism. Finally, we have computed the temperature variation of  $k_1, \sigma, k_e, S$ , PF, and  $ZT$ . The higher  $ZT$  values for spin-down channels have resulted from ultra-low  $k_e$ , and high PF. In short,  $\text{K}_2\text{W}(\text{Cl}/\text{Br})_6$  are potential thermoelectric and spintronic materials.

## Data availability

The datasets produced for current study would be available from Mr Mukaddar Sk on reasonable request.

## Conflicts of interest

The authors have no conflict of interest.

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